

CLAIMS

1. A hollow cathode sputtering target comprising an inner bottom face having a surface roughness of $Ra \leq 1.0 \mu m$.
- 5 2. A hollow cathode sputtering target comprising an inner bottom face having a surface roughness of $Ra \leq 0.5 \mu m$.
3. The hollow cathode sputtering target according to claim 1 or claim 2, comprising a bottom face having a surface roughness Ra equal to or less than a cylindrical inner peripheral face.
- 10 4. The hollow cathode sputtering target according to any one of claims 1 to 3, comprising a rough face at the outer peripheral edge.
5. The hollow cathode sputtering target according to claim 4, comprising a rough face formed by performing abrasive blasting to the outer peripheral edge.
6. The hollow cathode sputtering target according to any one of claims 1 to 5,
15 wherein the target is formed from a cladding material.
7. A surface finishing method of a hollow cathode sputtering target characterized in polishing and etching the bottom face of the target so as to make the surface roughness of the inner bottom face $Ra \leq 1.0 \mu m$.
8. A surface finishing method of a hollow cathode sputtering target
20 characterized in polishing and etching the bottom face of the target so as to make the surface roughness of the inner bottom face $Ra \leq 0.5 \mu m$.